Abstracts

First Demonstration of High-Power GaInP/GaAs HBT MMIC Power Amplifier with 9.9 W Output Power at X-Band

W. Liu, A. Khatibzadeh, T. Kim and J. Sweder. "First Demonstration of High-Power GaInP/GaAs HBT MMIC Power Amplifier with 9.9 W Output Power at X-Band." 1994 Microwave and Guided Wave Letters 4.9 (Sep. 1994 [MGWL]): 293-295.

We report for the first time the large-signal power performance of a MMIC amplifier based on GaInP/GaAs HBT's. A output power of 9.9 W and power-added efficiency of more than 30% are measured at X-band. These results compare favorably with those measured from AlGaAs/GaAs HBT's, demonstrating that GaInP/GaAs HBT's are suitable for microwave power applications.

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